Selection Guide

	-15	-20	-35	-45
Maximum Access Time (ns)	15	20	35	45
Maximum Operating Current (mA)	120	120	120	120
Maximum CMOS Standby Current (mA)	40	20	20	20

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature ..... –65°C to +150°C

Ambient Temperature with Power Applied ..... –55°C to +125°C

Supply Voltage to Ground Potential (Pin 28 to Pin 14) ..... –0.5V to +7.0V

DC Voltage Applied to Outputs in High Z State ..... –0.5V to +7.0V

DC Input Voltage ..... –3.0V to +7.0V

Output Current into Outputs (LOW) ..... 20 mA

Static Discharge Voltage ..... >2001V (per MIL-STD-883, Method 3015)

Latch-Up Current ..... >200 mA

Operating Range

Range	Ambient Temperature	V_{CC}
Commercial	0°C to +70°C	5V ± 10%

Electrical Characteristics Over the Operating Range[2]

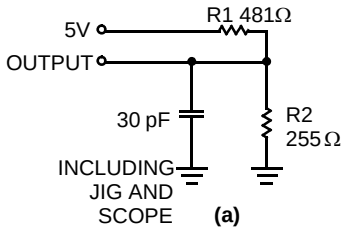
Parameter	Description	Test Conditions	-15		-20		-35, -45		Unit
			Min.	Max.	Min.	Max.	Min.	Max.	
V_{OH}	Output HIGH Voltage	V_{CC} = Min., I_{OH} = –4.0 mA	2.4		2.4		2.4		V
V_{OL}	Output LOW Voltage	V_{CC} = Min., I_{OL} = 8.0 mA		0.4		0.4		0.4	V
V_{IH}	Input HIGH Voltage		2.2	V_{CC}	2.2	V_{CC}	2.2	V_{CC}	V
V_{IL}	Input LOW Voltage[3]		–0.5	0.8	–0.5	0.8	–0.5	0.8	V
I_{IX}	Input Leakage Current	GND ≤ V_I ≤ V_{CC}	–10	+10	–10	+10	–10	+10	µA
I_{OZ}	Output Leakage Current	GND ≤ V_I ≤ V_{CC} Output Disabled	–10	+10	–10	+10	–10	+10	µA
I_{CC}	V_{CC} Operating Supply Current	V_{CC} = Max. I_{OUT} = 0 mA		120		120		120	mA
I_{SB1}	Automatic $\overline{CE}$ Power-Down Current	Max. V_{CC}, $\overline{CE}$ ≥ V_{IH}, Min. Duty Cycle = 100%		40		40		20	mA
I_{SB2}	Automatic $\overline{CE}$ Power-Down Current	Max. V_{CC}, $\overline{CE}_1$ ≥ V_{CC}–0.3V, V_{IN} ≥ V_{CC}–0.3V or V_{IN} ≤ 0.3V		40		20		20	mA

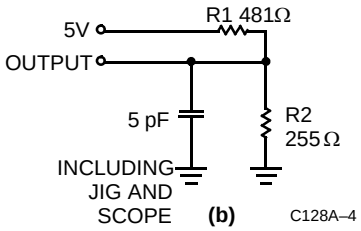
Notes:
1. T_A is the "instant on" case temperature.
2. See the last page of this specification for Group A subgroup testing information.
3. V_{IL} (min.) = –3.0V for pulse durations less than 30 ns.

Capacitance[4]

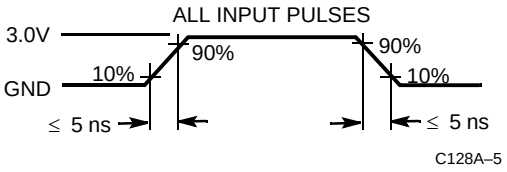
Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	T_A = 25°C, f = 1 MHz, V_{CC} = 5.0V	10	pF
C_{OUT}	Output Capacitance		10	pF

AC Test Loads and Waveforms



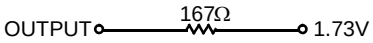


C128A–4



C128A–5

Equivalent to: THÉVENIN EQUIVALENT



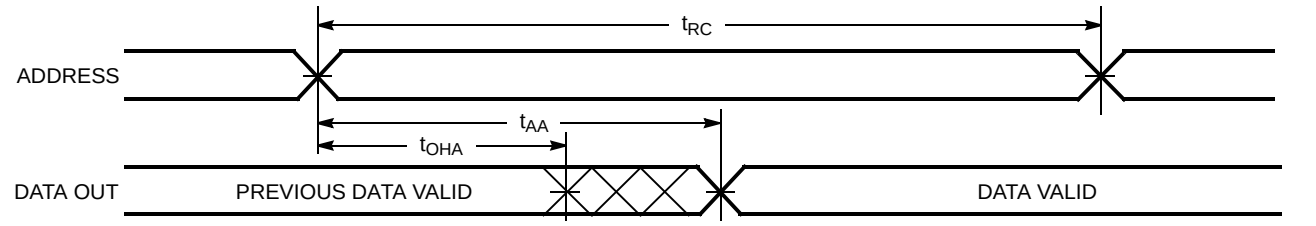
Switching Characteristics Over the Operating Range[2, 5]

Parameter	Description	-15		-20		-35		-45		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
READ CYCLE										
t_{RC}	Read Cycle Time	15		20		35		45		ns
t_{AA}	Address to Data Valid		15		20		35		45	ns
t_{OHA}	Data Hold from Address Change	5		5		5		5		ns
t_{ACE}	$\overline{CE}$ LOW to Data Valid		15		20		35		45	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid		10		10		15		20	ns
t_{LZOE}	$\overline{OE}$ LOW to Low Z	3		3		3		3		ns
t_{HZOE}	$\overline{OE}$ HIGH to High Z[6]		8		8		12		15	ns
t_{LZCE}	$\overline{CE}$ LOW to Low Z[7]	5		5		5		5		ns
t_{HZCE}	$\overline{CE}$ HIGH to High Z[6, 7]		8		8		15		15	ns
t_{PU}	$\overline{CE}$ LOW to Power-Up	0		0		0		0		ns
t_{PD}	$\overline{CE}$ HIGH to Power-Down		15		20		20		25	ns
WRITE CYCLE[8]										
t_{WC}	Write Cycle Time	15		20		25		40		ns
t_{SCE}	$\overline{CE}$ LOW to Write End	12		15		25		30		ns
t_{AW}	Address Set-Up to Write End	12		15		25		30		ns
t_{HA}	Address Hold from Write End	0		0		0		0		ns
t_{SA}	Address Set-Up to Write Start	0		0		0		0		ns
t_{PWE}	$\overline{WE}$ Pulse Width	12		15		20		20		ns
t_{SD}	Data Set-Up to Write End	10		10		15		15		ns
t_{HD}	Data Hold from Write End	0		0		0		0		ns
t_{HZWE}	$\overline{WE}$ LOW to High Z[6]		7		7		10		15	ns
t_{LZWE}	$\overline{WE}$ HIGH to Low Z	5		5		5		5		ns

Notes:
4. Tested initially and after any design or process changes that may affect these parameters
5. Test conditions assume signal transition time of 5 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V, and output loading of the specified I_{OL}/I_{OH} and 30-pF load capacitance.
6. t_{HZOE}, t_{HZCE}, and t_{HZWE} are specified with C_L = 5 pF as in part (b) of AC Test Loads. Transition is measured ±500 mV from steady state voltage.
7. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE} for any given device.
8. The internal write time of the memory is defined by the overlap of $\overline{CE}$ LOW and $\overline{WE}$ LOW. Both signals must be LOW to initiate a write and either signal can terminate a write by going HIGH. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write.

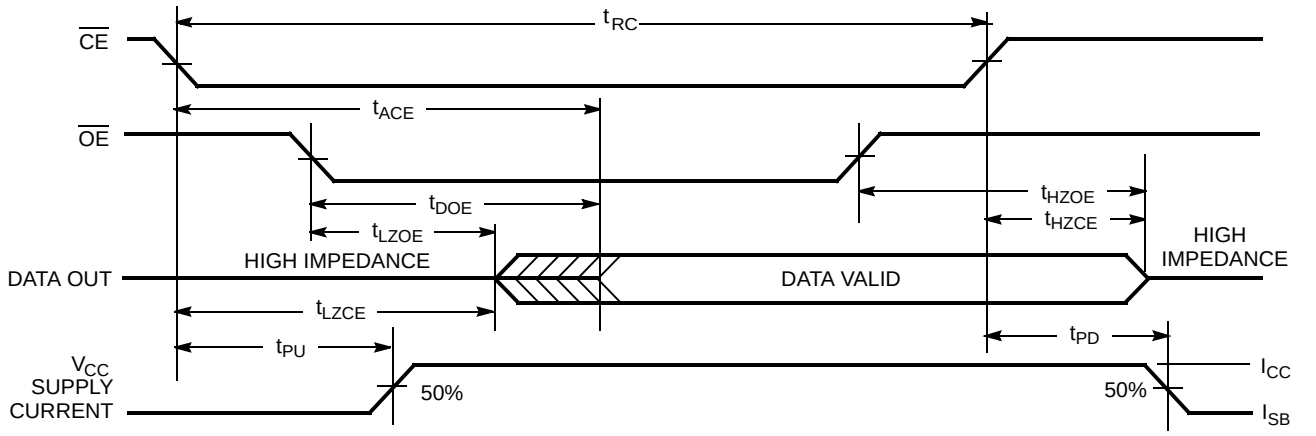
Switching Waveforms

Read Cycle No. 1[9, 10]



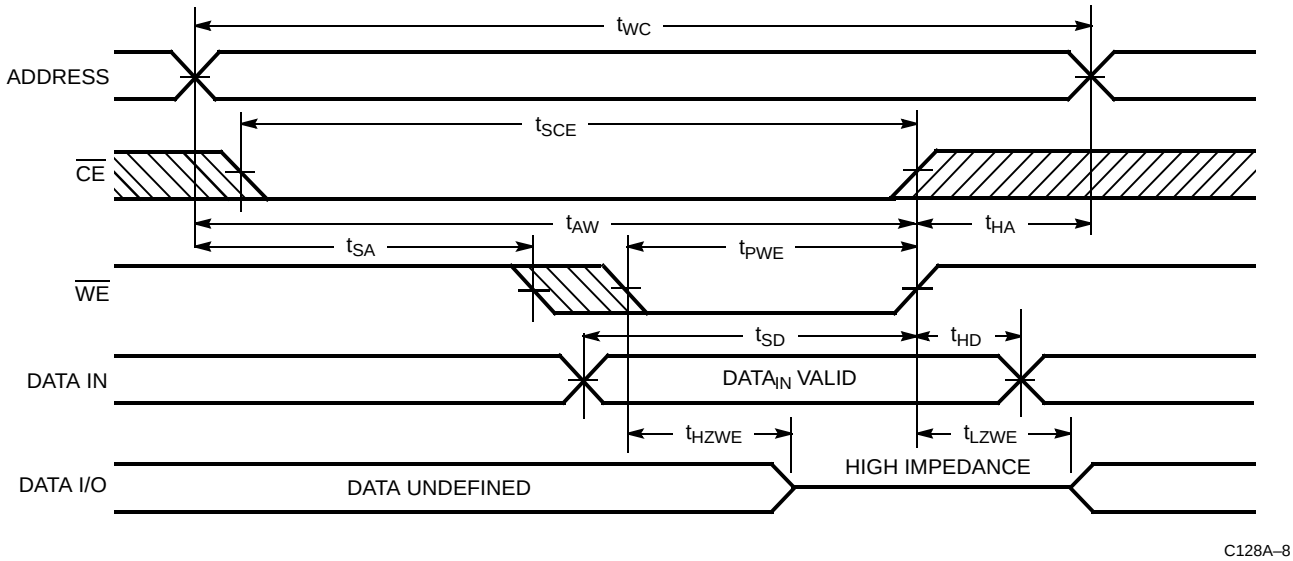
C128A–6

Read Cycle No. 2[9, 11]



C128A–7

Write Cycle No. 1 ($\overline{WE}$ Controlled)[8]

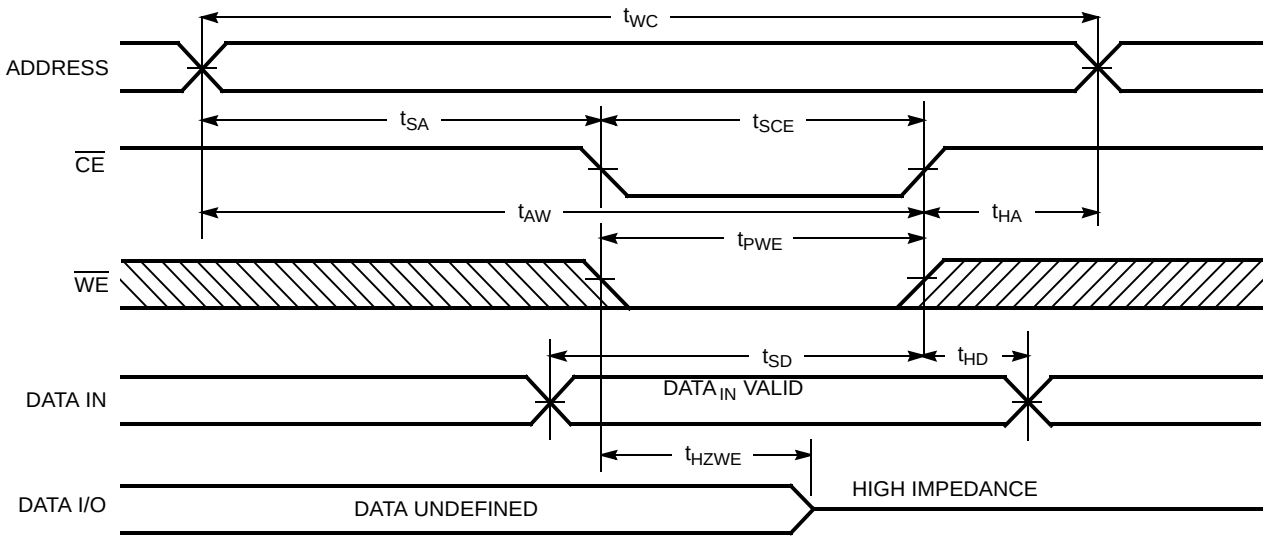


C128A–8

Notes:
9. $\overline{WE}$ is HIGH for read cycle.
10. Device is continuously selected. $\overline{OE}$, $\overline{CE}$ = V_{IL}.
11. Address valid prior to or coincident with $\overline{CE}$ transition LOW.

Switching Waveforms (continued)

Write Cycle No. 2 ($\overline{CE}$ Controlled)[8, 12, 13]

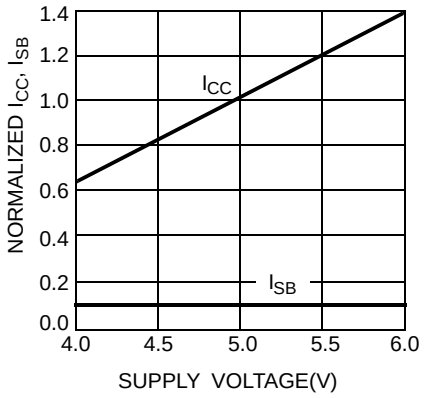


C128A–9

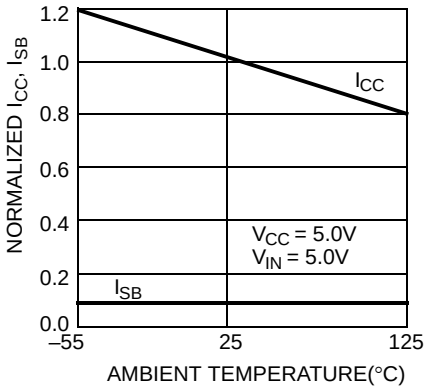
Notes:
12. Data I/O pins enter high-impedance state, as shown, when $\overline{OE}$ is held LOW during write.
13. If $\overline{CE}$ goes HIGH simultaneously with $\overline{WE}$ HIGH, the output remains in a high-impedance state.

Typical DC and AC Characteristics

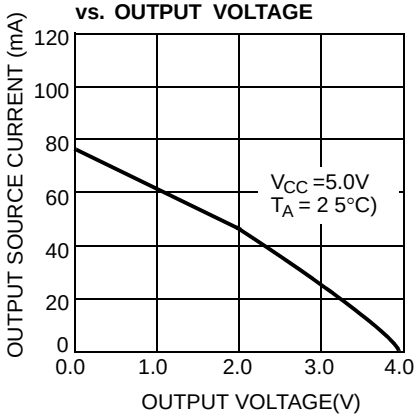
NORMALIZED SUPPLY CURRENT vs. SUPPLY VOLTAGE



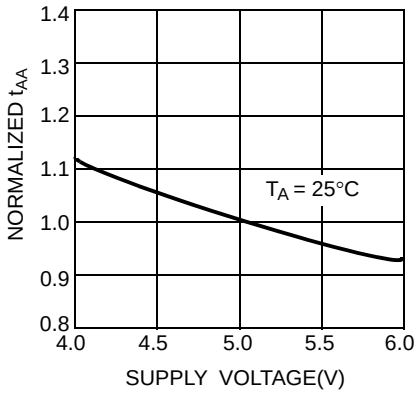
NORMALIZED SUPPLY CURRENT vs. AMBIENT TEMPERATURE



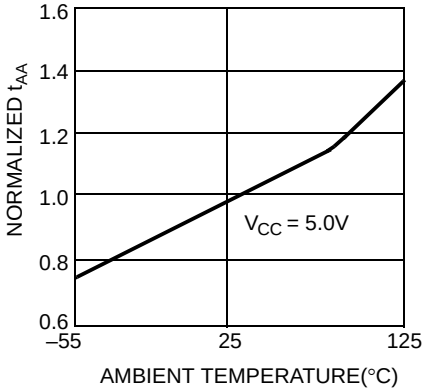
OUTPUT SOURCE CURRENT vs. OUTPUT VOLTAGE



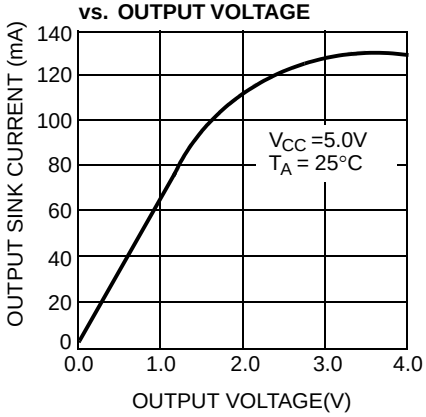
NORMALIZED ACCESS TIME vs. SUPPLY VOLTAGE



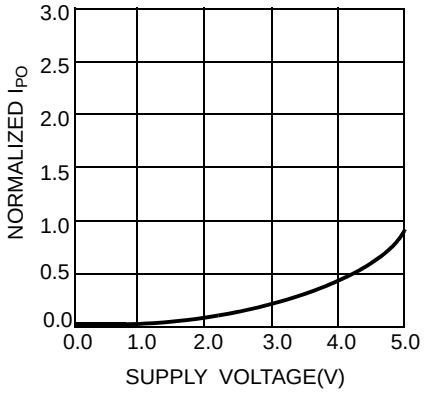
NORMALIZED ACCESS TIME vs. AMBIENT TEMPERATURE



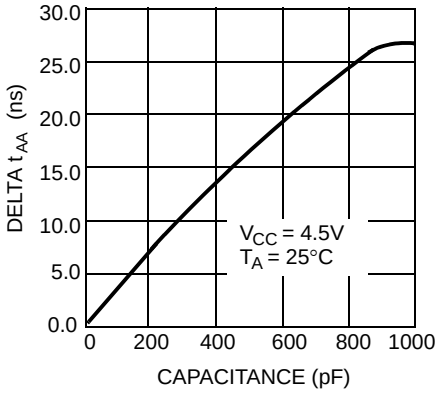
OUTPUT SINK CURRENT vs. OUTPUT VOLTAGE



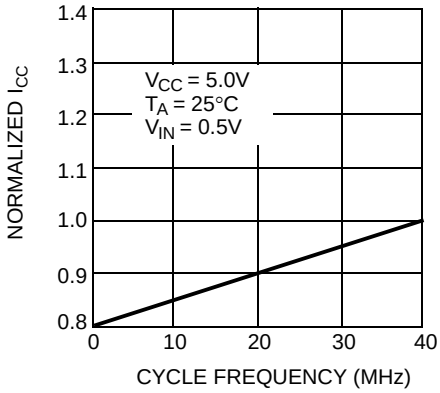
TYPICAL POWER-ON CURRENT vs. SUPPLY VOLTAGE



TYPICAL ACCESS TIME CHANGE vs. OUTPUT LOADING



NORMALIZED I_{CC} vs. CYCLE TIME



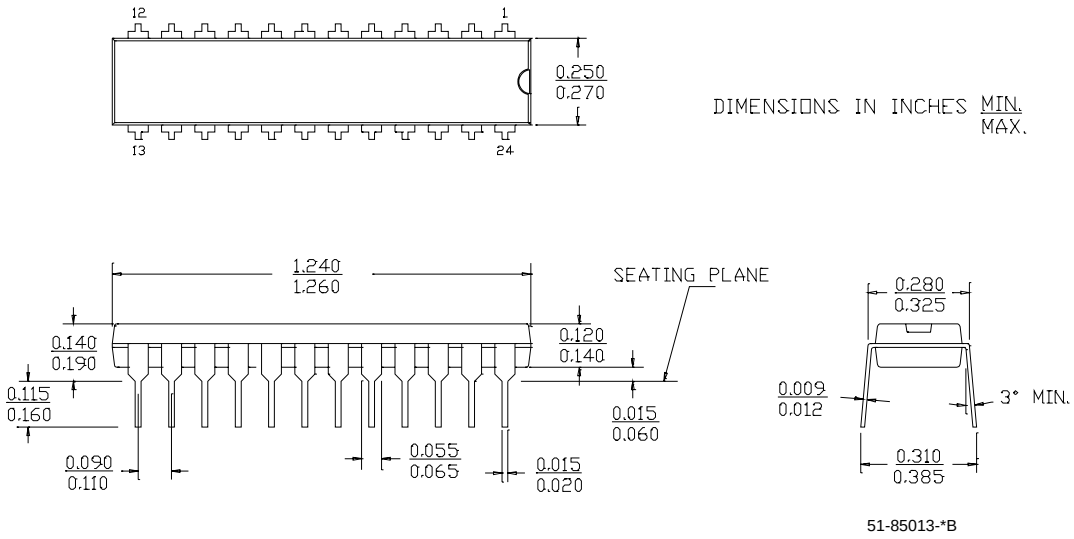
Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
15	CY7C128A-15PC	51-85013	24-pin (300-Mil) Molded DIP	Commercial
	CY7C128A-15VC	51-85030	24-pin Molded SOJ	
	CY7C128A-15VXC		24-pin Molded SOJ	
20	CY7C128A-20VXC	51-85030	24-pin Molded SOJ (Pb-free)	Commercial
35	CY7C128A-35VC	51-85030	24-pin Molded SOJ	Commercial
45	CY7C128A-45PC	51-85013	24-pin (300-Mil) Molded DIP	Commercial

Please contact local sales representative regarding availability of these parts

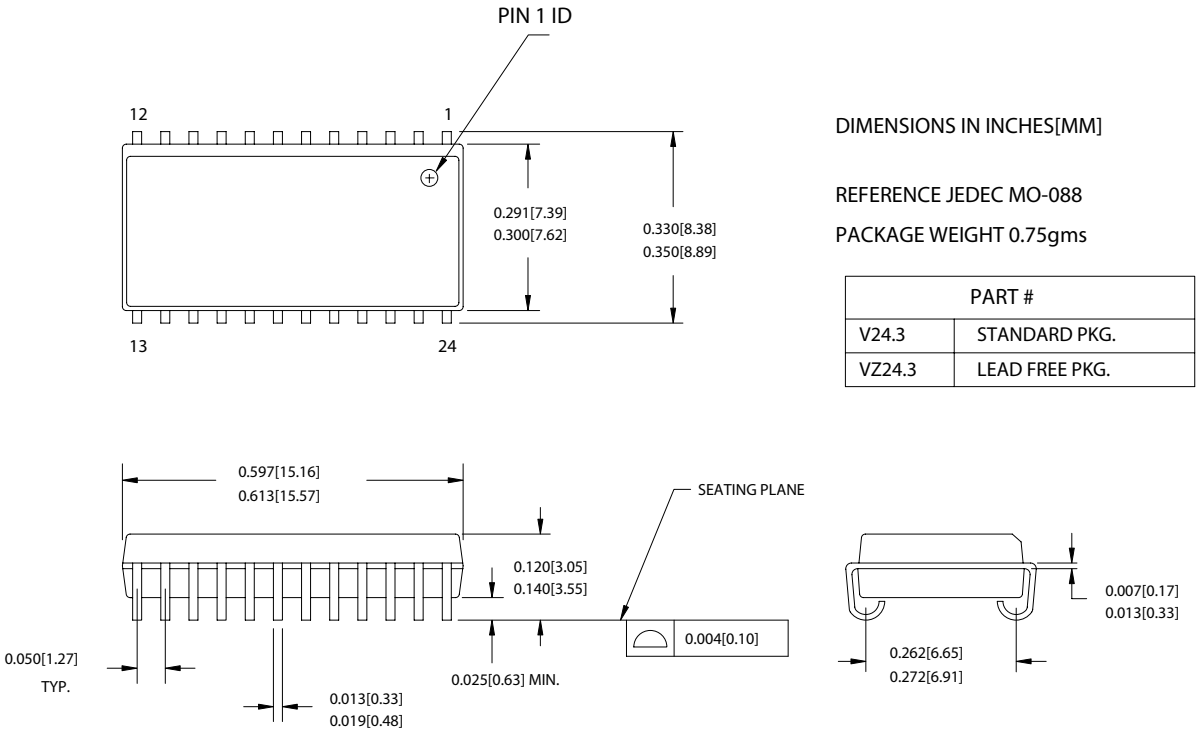
Package Diagrams

24-pin (300-Mil) Molded DIP (51-85013)



Package Diagrams (continued)

24-pin (300-mil) SOJ (51-85030)



DIMENSIONS IN INCHES[MM] MIN.
MAX.

REFERENCE JEDEC MO-088

PACKAGE WEIGHT 0.75gms

PART #	
V24.3	STANDARD PKG.
VZ24.3	LEAD FREE PKG.

51-85030-*B

Document History Page

Document Title: CY7C128A 2K x 8 Static RAM Document Number: 38-05028				
REV.	**ECN NO.**	**Issue Date**	**Orig. of Change**	**Description of Change**
**	106814	09/10/01	SZV	Change from Spec number: 38-00094 to 38-05028
*A	493543	See ECN	NXR	Removed 25 ns speed bin Removed Military Operating Range Changed the description of I_{IX} from Input Load Current to Input Leakage Current in DC Electrical Characteristics table Removed I_{OS} parameter from DC Electrical Characteristics table Updated ordering Information Table